FAIRCHILD
SEMICONDUCTOR®

IGBT

FGA25N120AND

General Description

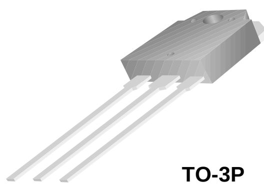
Employing NPT technology, Fairchild's AND series of IGBTs provides low conduction and switching losses. The AND series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

Features

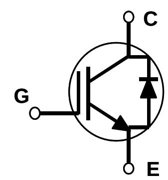
- High speed switching
- Low saturation voltage : $V_{CE(sat)}$ = 2.5 V @ I_C = 25A
- High input impedance
- CO-PAK, IGBT with FRD : t_{rr} = 235ns (typ.)

Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.



TO-3P



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Description		FGA25N120AND	Units
V_{CES}	Collector-Emitter Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	40	A
	Collector Current	@ T_C = 100°C	25	A
$I_{CM\ (1)}$	Pulsed Collector Current		75	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	25	A
I_{FM}	Diode Maximum Forward Current		150	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	310	W
	Maximum Power Dissipation	@ T_C = 100°C	125	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	0.4	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	2.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 3mA	1200	--	--	V
ΔB_{VCES}/ ΔT_J	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0V, I_C = 3mA	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0V	--	--	3	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0V	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 25mA, V_{CE} = V_{GE}	3.5	5.5	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 25A, V_{GE} = 15V	--	2.5	3.2	V
		I_C = 25A, V_{GE} = 15V, T_C = 125°C	--	2.9	--	V
		I_C = 40A, V_{GE} = 15V	--	3.1	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	--	2100	--	pF
C_{oes}	Output Capacitance		--	180	--	pF
C_{res}	Reverse Transfer Capacitance		--	90	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 25A, R_G = 10Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	--	60	--	ns
t_r	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	170	--	ns
t_f	Fall Time		--	45	90	ns
E_{on}	Turn-On Switching Loss		--	4.8	7.2	mJ
E_{off}	Turn-Off Switching Loss		--	1.0	1.5	mJ
E_{ts}	Total Switching Loss		--	5.7	8.7	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 25A, R_G = 10Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	--	60	--	ns
t_r	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	180	--	ns
t_f	Fall Time		--	70	--	ns
E_{on}	Turn-On Switching Loss		--	5.5	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.4	--	mJ
E_{ts}	Total Switching Loss		--	6.9	--	mJ
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 25A, V_{GE} = 15V	--	200	300	nC
Q_{ge}	Gate-Emitter Charge		--	15	23	nC
Q_{gc}	Gate-Collector Charge		--	105	160	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	I_F = 25A	T_C = 25°C	--	2.0	3.0	V
			T_C = 125°C	--	2.1	--	
t_{rr}	Diode Reverse Recovery Time	I_F = 25A, dI/dt = 200 A/µs	T_C = 25°C	--	235	350	ns
			T_C = 125°C	--	300	--	
I_{rr}	Diode Peak Reverse Recovery Current		T_C = 25°C	--	27	40	A
			T_C = 125°C	--	31	--	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	--	3130	4700	nC
			T_C = 125°C	--	4650	--	

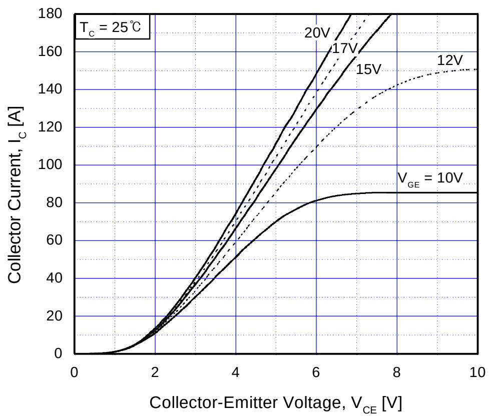


Fig 1. Typical Output Characteristics

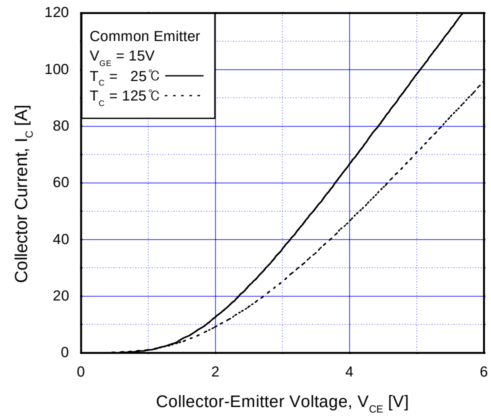


Fig 2. Typical Saturation Voltage Characteristics

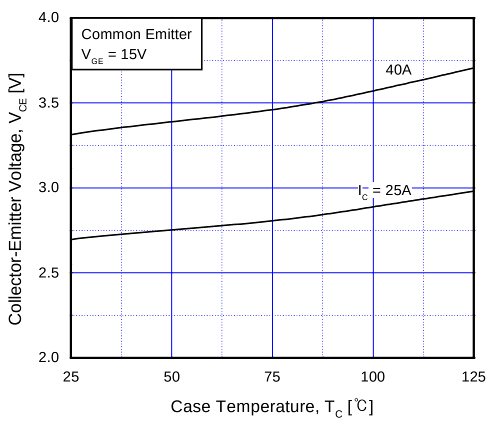


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

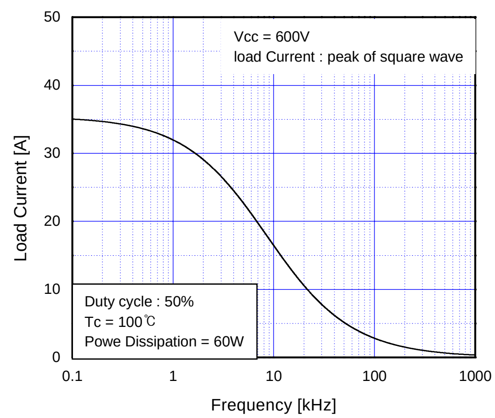


Fig 4. Load Current vs. Frequency

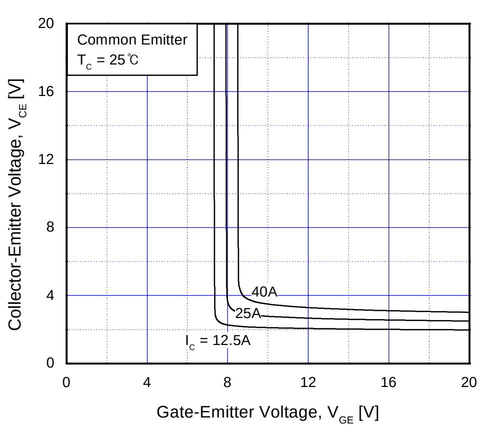


Fig 5. Saturation Voltage vs. V_{GE}

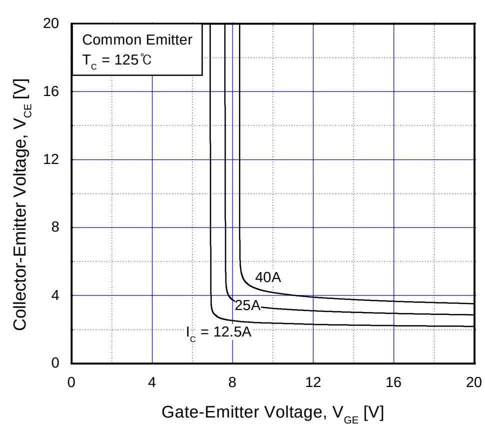


Fig 6. Saturation Voltage vs. V_{GE}

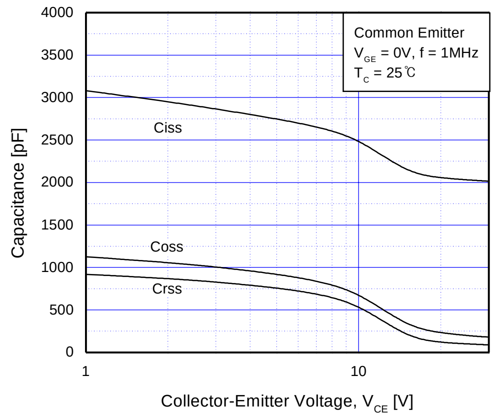


Fig 7. Capacitance Characteristics

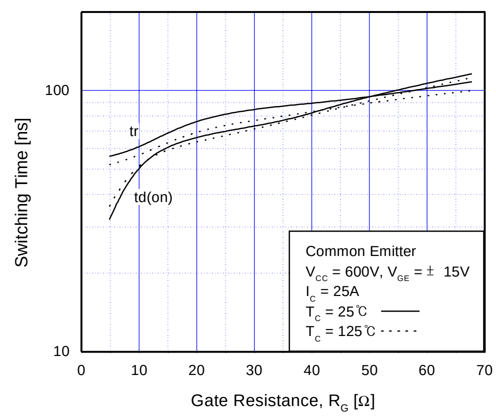


Fig 8. Turn-On Characteristics vs. Gate Resistance

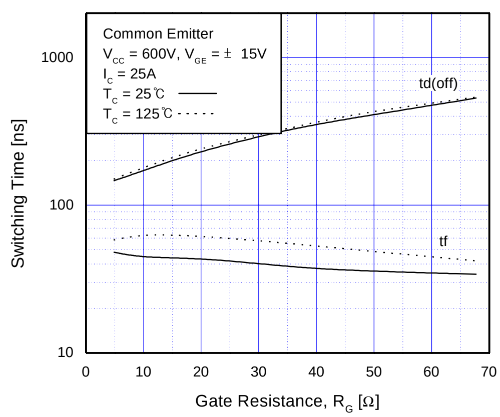


Fig 9. Turn-Off Characteristics vs. Gate Resistance

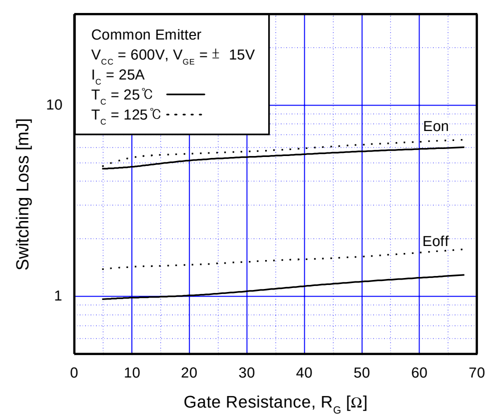


Fig 10. Switching Loss vs. Gate Resistance

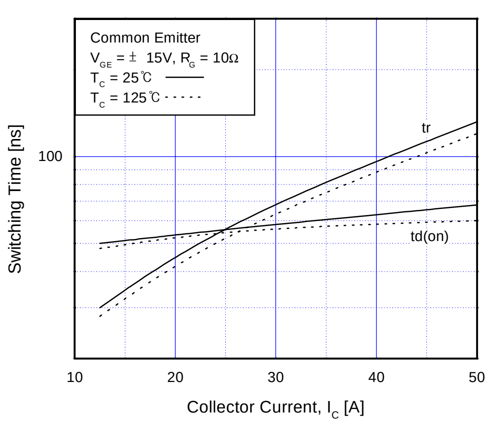


Fig 11. Turn-On Characteristics vs. Collector Current

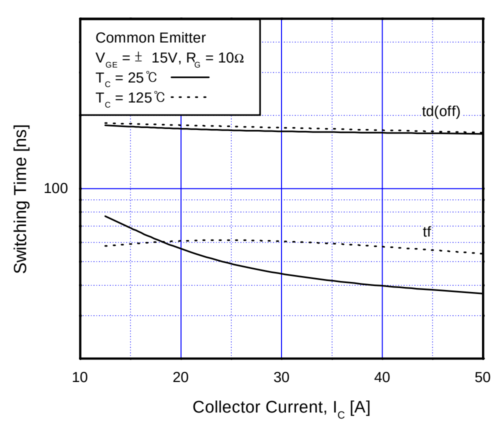


Fig 12. Turn-Off Characteristics vs. Collector Current

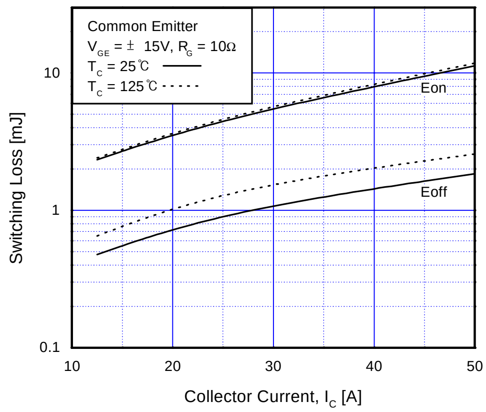


Fig 13. Switching Loss vs. Collector Current

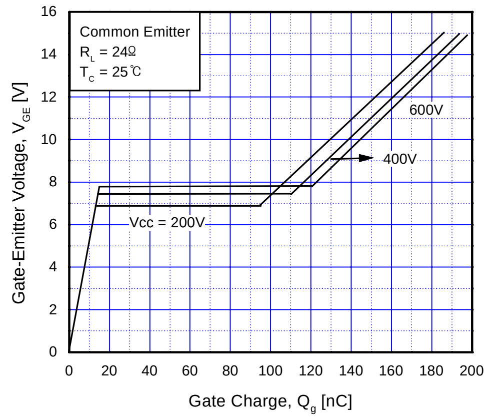


Fig 14. Gate Charge Characteristics

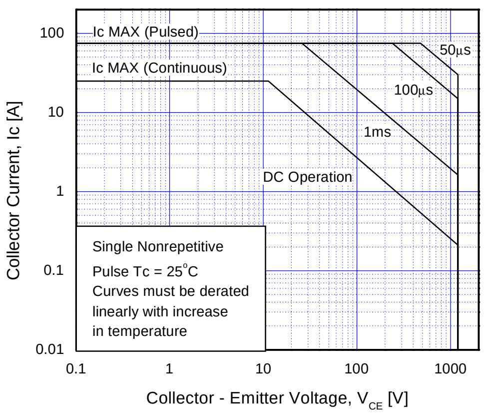


Fig 15. SOA Characteristics

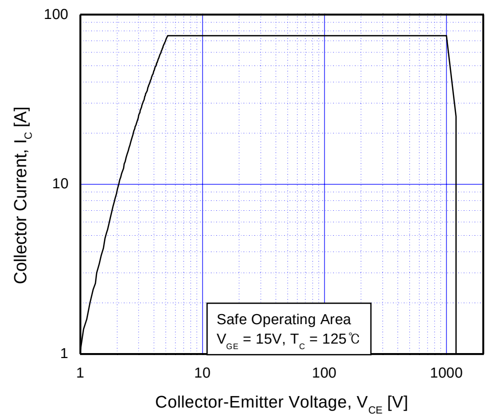


Fig 16. Turn-Off SOA

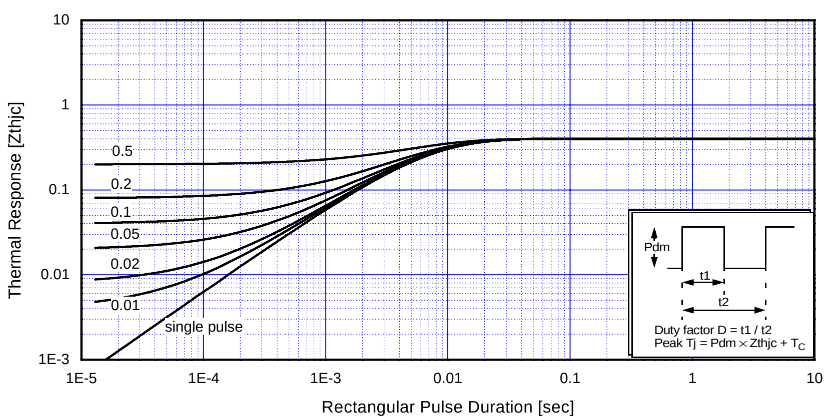


Fig 17. Transient Thermal Impedance of IGBT

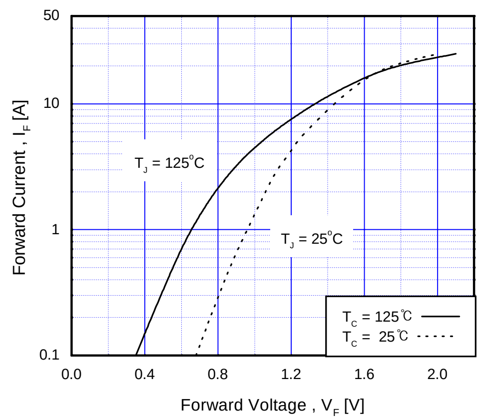


Fig 18. Forward Characteristics

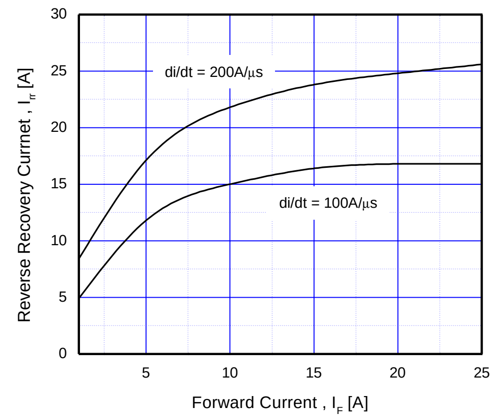


Fig 19. Reverse Recovery Current

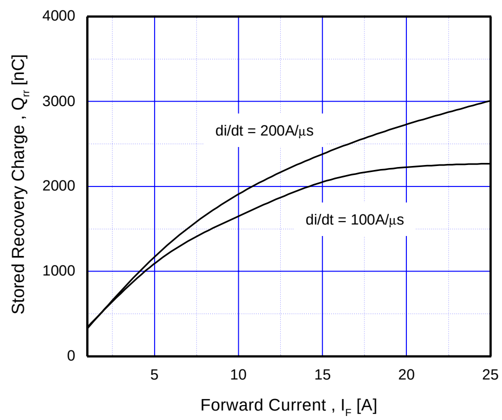


Fig 20. Stored Charge

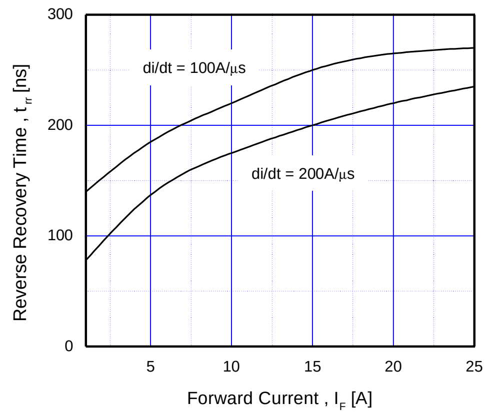
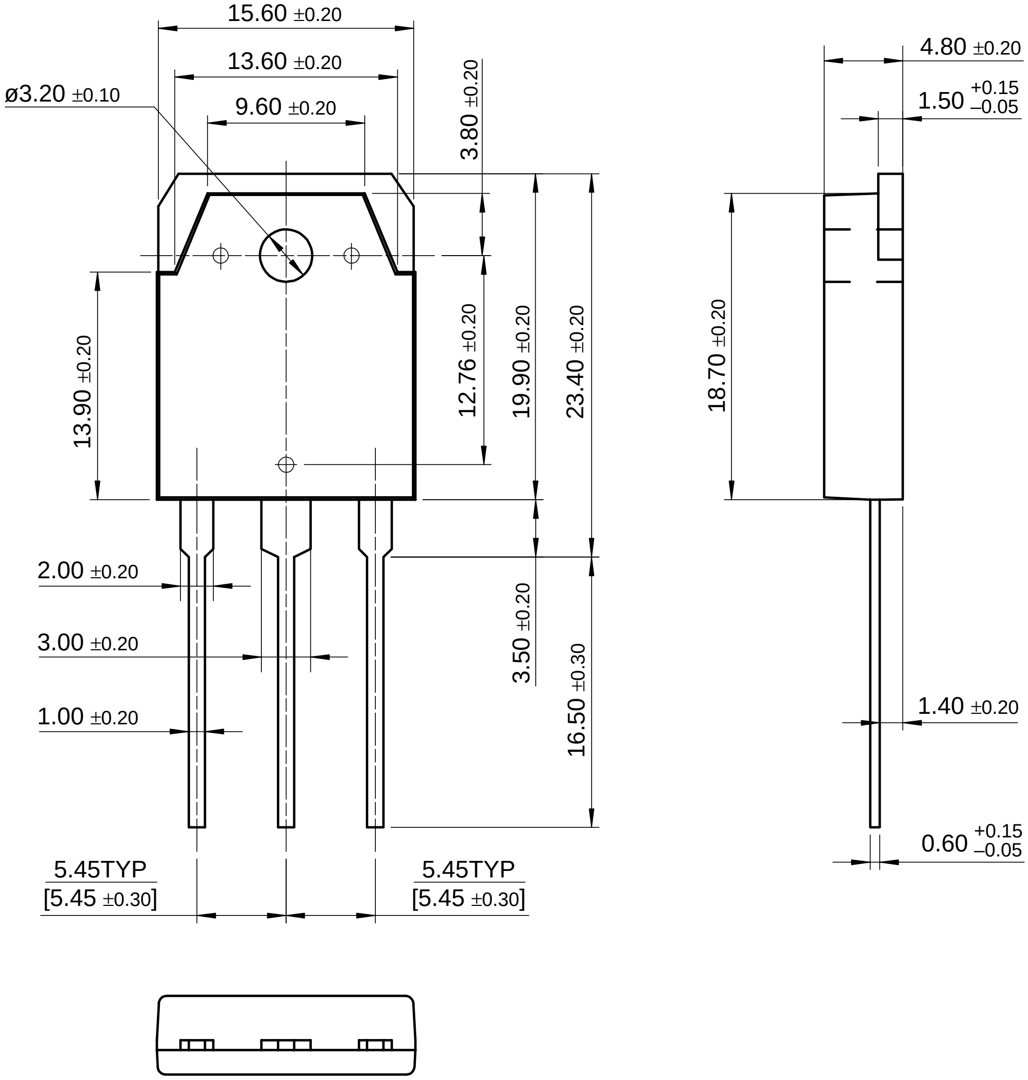


Fig 21. Reverse Recovery Time

Package Dimension

TO-3P



Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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